TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA573FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

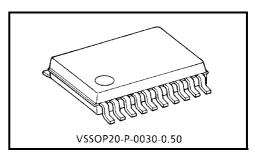
The TC7MA573FK is a high performance CMOS octal D-type latch. Designed for use in $1.8\ V,\ 2.5\ V$ or $3.3\ V$ systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V.$

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 4.2 \text{ ns (max)} (V_{CC} = 3.0 \sim 3.6 \text{ V})$

 $t_{pd} = 4.7 \text{ ns (max) (VCC} = 2.3 \sim 2.7 \text{ V)}$

 $t_{pd} = 9.4 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 24 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 6 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200

Human body model $> \pm 2000 \text{ V}$

- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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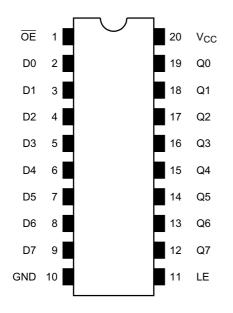
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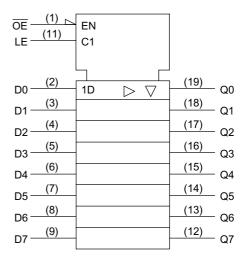
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Pin Assignment (top view)



IEC Logic Level



Truth Table

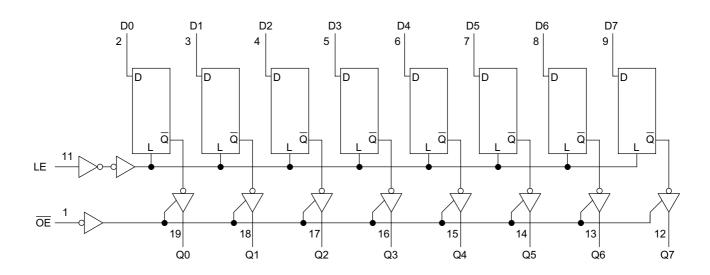
	Outputs		
ŌĒ	LE	D	Outputs
Н	Х	Х	Z
L	L	Х	Q _n
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

Q_n: Q outputs are latched at the time when the LE inputs is taken to a low logic level.

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	V
DC output voltage	V	-0.5~4.6 (Note1)	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5 (Note2)	
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note3)	mA
DC output current	Гоит	±50	mA
Power dissipation	PD	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Characteristics Symbol Rating		Unit
Cupply voltage	V	1.8~3.6	V
Supply voltage	Vcc	1.2~3.6 (Note4)	V
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	Vour	0~3.6 (Note5)	V
Output voltage	V _{OUT}	0~V _{CC} (Note6)	V
		±24 (Note7)	
Output current	I _{OH} /I _{OL}	±18 (Note8)	mA
		±6 (Note9)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$

Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$ Note9: $V_{CC} = 1.8 \text{ V}$

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Character	stics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit
Innut valtage	High level	V _{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2		
	High level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -12 mA	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -24 mA	3.0	2.2	_	V
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
	Low level	VOI		I _{OL} = 12 mA	2.7	_	0.4	
	Low level	VOL.		I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
3-state output off-si	tate current	l _{OZ}	V _{IN} = V _{IH} or V _{IL}		2.7~3.6		+10.0	μА
3-state output on-s	3-state output off-state current		V _{OUT} = 0~3.6 V		2.7~3.0		±10.0	
Power off leakage	current	I _{OFF}	V_{IN} , $V_{OUT} = 0~3.6 V$		0	_	10.0	μΑ
			$V_{IN} = V_{CC}$ or GND		2.7~3.6	_	20.0	
Quiescent supply c	urrent	I _{CC} v	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$ (per	input)	2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Tes	st Condition	V _{CC} (V)	Min	Max	Unit		
Innut voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V		
Input voltage	Low level	V _{IL}		_	2.3~2.7		0.7	V		
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_			
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.3	2.0	_	1		
					I _{OH} = -12 mA	2.3	1.8	_		
Output voltage				$I_{OH} = -18 \text{ mA}$	2.3	1.7	_	V		
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2			
	Low level	V_{OL}		$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6			
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V	•	2.3~2.7	_	±5.0	μА		
3-state output off-state current		1	$V_{IN} = V_{IH}$ or V_{IL}		V _{IN} = V _{IH} or V _{IL}	2.3~2.7		. 40.0		
		loz	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μΑ		
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ		
Outro and according accorded		laa	V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	^		
Quiescent supply	Current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ		



DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltogo	High level	V _{IH}		_		0.7× V _{CC}	_	V
Input voltage	Low level	V _{IL}		_	1.8~2.3		0.2× V _{CC}	٧
	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -100 \mu A$	1.8	V _{CC} - 0.2		
Output voltage				$I_{OH} = -6 \text{ mA}$	1.8	1.4	_	V
	Low level	VOI	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \mu A$	1.8	_	0.2	
	LOW level	VOL		I _{OL} = 6 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μΑ
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μΑ
Power off leakage of	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quiescent supply co	0		$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	μА
Quiescent supply co	an c nt	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.$	6 V	1.8	—	±20.0	μΑ



AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$)

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
Onaractoristics	Cymbol	rest condition	V _{CC} (V)	IVIIII	IVIAX	Offic
	.		1.8	1.5	9.4	
Propagation delay time (D-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.7	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.2	
	4		1.8	1.5	9.8	
Propagation delay time (LE-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.9	ns
	t _{pHL}		3.3 ± 0.3	0.6	4.2	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	5.5	ns
	t _{pZH}		3.3 ± 0.3	0.6	4.5	
		Figure 1, Figure 3	1.8	1.5	6.5	ns
3-state output disable time	t _{pLZ}		2.5 ± 0.2	0.8	3.6	
	t _{pHZ}		3.3 ± 0.3	0.6	3.3	
			1.8	4.0	_	
Minimum pulse width	t _{w (H)}	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	
Output to output skew	t _{osLH}	(Note11)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Syllibol			V _{CC} (V)	τyp.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	e12)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	3.3	0.8	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	e12)	1.8	-0.25	
Quiet output minimum dynamic V _{OL}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	2.5	-0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Not	e12)	1.8	1.5	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	e12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Syllibol	rest condition	V _{CC} (V)	τyp.	Offic
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \text{ MHz}$ (Note	3) 1.8, 2.5, 3.3	20	pF

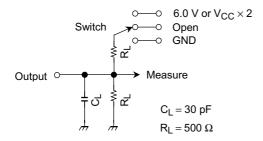
Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$



AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}			
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

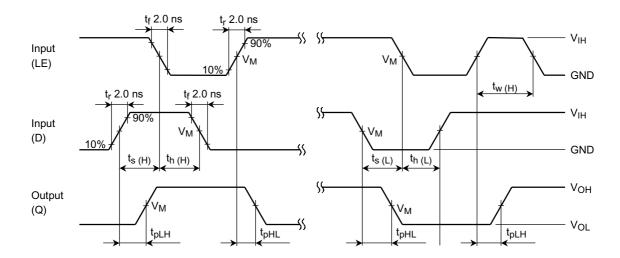


Figure 2 t_{pLH} , t_{pHL} , t_{w} , t_{s} , t_{h}

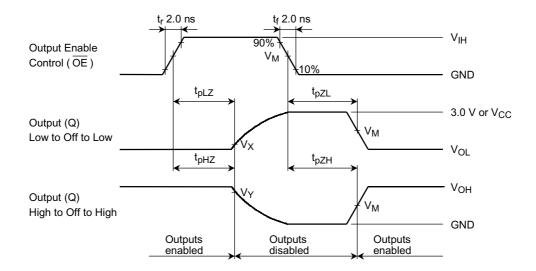
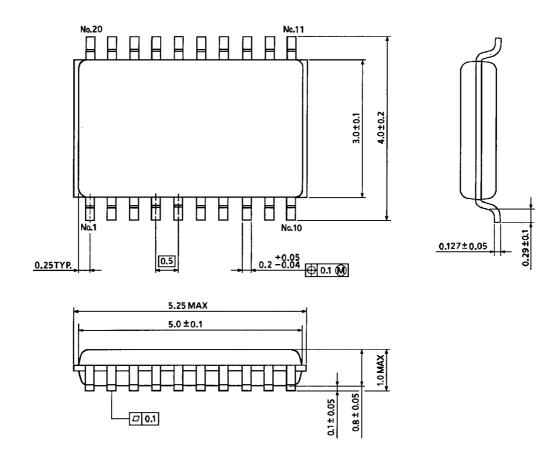


Figure 3 $t_{pLZ},\,t_{pHZ},\,t_{pZL},\,t_{pZH}$

Cumbal		V _{CC}	
Symbol	$3.3 \pm 0.3 \text{ V}$	2.5 ± 0.2 V	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions



Weight: 0.03 g (typ.)